

A study on the crystallization speed and thermal stability of N-doped $\text{Ge}_2\text{Sb}_2\text{Te}_5$ thin film during amorphous-to-crystalline phase transition.

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In this work, we evaluated crystallization speed, thermal stability and optical property of the N-doped $\text{Ge}_2\text{Sb}_2\text{Te}_5$ (GST) thin film, a candidate material for application to a phase-change random access memory (PRAM). The 200-nm-thick GST and N-GST films were deposited on p-type (100) Si and glass substrates using rf reactive sputtering at room temperature. Amorphous-to-crystalline phase transformation of GST and N-GST films was investigated by X-ray diffraction (XRD). The addition of N caused an increase of the crystallization temperature (T_c), which means the enhancement of thermal stability for amorphous phase. Changes in the optical transmittance and sheet resistance (R_s) of N-GST were observed using an UV-vis-IR spectrophotometer and 4-point probe, respectively. It was found that the added N causes the increase of R_s for both crystalline and amorphous phases and the optical energy gap (E_{OP}). In particular, a high R_s is useful to reduce programming current. In addition, a speed of amorphous-to-crystalline transition and the surface morphology were evaluated by using a nano-pulse scanner (beam diameter $< 2 \mu\text{m}$) and atomic force microscope, respectively. Conclusively, while the N-doping into GST causes the increase of T_c , R_s and E_{OP} , it accompanies a decrease of crystallization speed.

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1. Introduction

The demand for non-volatile memories has increased as the market for mobile instruments, such as personal digital assistants (PDA), cellular phone, electronic digital cameras and others has expanded.[1] With its many advantages over other existing memories, a phase change random access memory (PRAM) is considered to be mostly close to a practical utilization and promising candidate as the next generation memory due to many advantages such as high speed, low power, high density, and low cost.[2] The PRAM is based on the reversible phase transformation between amorphous and crystalline states by local heating with a nanosecond current. There have been great efforts on developing new phase-change materials and understanding the phase transformation phenomena in phase-change materials. The pseudo-binary $\text{Ge}_2\text{Sb}_2\text{Te}_5$ (GST) films have been utilized as a phase-change recording medium.[3] However, there are several problems associated with GST material for high density PRAM devices such as high reset current, thermal stability in amorphous state, relatively.[4] In particular, a high resistance in the crystalline phase is necessary to reduce electrical current.

Thus, nitrogen-doped GST (N-GST) films have been studied with a focus on increasing the electrical resistance of phase change materials.[5] When nitrogen is doped into a GST film, it exists in the forms of nitride or N_2 molecules, which suppresses crystalline grain growth.[6] However, most studies on the effect of N-doping into

$\text{Ge}_2\text{Sb}_2\text{Te}_5$ film have been concentrated on the macroscopic viewpoint of electrical and optical properties.[7-8] The role of doped nitrogen on the microscopic viewpoint of crystallization speed has not yet been reported.

In this study, we investigated that crystallization speed as well as thermal stability and optical property of N-doped GST in comparison with pseudo-binary GST.

2. Experimental details

The 200-nm-thick GST and N-GST films were deposited on p-type (100) Si and glass substrate by rf reactive sputtering at room temperature using $\text{Ge}_2\text{Sb}_2\text{Te}_5$ composite target. The sputtering was conducted under a power of 50 W, base pressure of 4×10^{-8} Torr and working pressure of 5×10^{-3} Torr. Through the scanning-electron microscope and energy-dispersive X-ray spectroscopy (SEM-EDX) analysis, we confirmed that the composition and thickness of films are under the 5% error range. However we didn't indicate the data in this paper. Nitrogen doping was carried out by adding N_2 gas into Ar gas within a range of 0-6 sccm for controlling the nitrogen contents in the GST films while the total gas flow rate was fixed at 40 sccm.

Sputtered films were isothermally annealed in a N_2 atmosphere for 10 min. The isothermal structural phase changes were characterized using X-ray diffraction (XRD, X'pert PRO, Phillips) operated at 40 kV and 40 mA using

Cu $K\alpha$ radiation. XRD measurements were performed for GST and N-GST thin films annealed from 140 °C to 400 °C. The optical transmittance (T_{OP}) was measured in the wavelength (λ) range of 800-3000 nm using a UV-vis-NIR spectrophotometer (Shimadzu, U-3501). The optical absorption coefficient (α) was then calculated using the general relation of $\alpha = -\ln(T_{OP})/d$ and the E_{OP} was also evaluated using the absorption property expressed as $\alpha h\nu \propto (h\nu - E_{OP})^2$. The sheet resistances (R_S) of the films were measured with a 4-point probe (CNT-series). The nano-pulse illumination was performed using a nano-pulse scanner with a laser diode of $\lambda = 650$ nm (beam diameter < 2 μm). Speed of the amorphous-to-crystalline phase transition was evaluated by detecting the response reflection signals, $\Delta R = R_2 - R_1$, where R_1 and R_2 are the intensities before and after illumination, respectively. In this work, ΔR was measured over a laser power (P) range of 1 ~ 17 mW and a pulse duration (t) range of 10 ~ 460 ns. In addition, the effects of N doping on the surface morphology and roughness of the films were observed by atomic force microscope (AFM).

3. Results and discussion

The XRD results for 200-nm-thick GST and N-GST thin films are shown in Fig. 1, where N_2 gas flow rates of

(b), (c) and (d) were approximately 2, 4 and 6 sccm, respectively. As shown in Fig. 1(a), as-deposited and 140 °C-annealed GST thin films did not show any XRD peak, indicating amorphous phase. In general, the $\text{Ge}_2\text{Sb}_2\text{Te}_5$ thin film exhibits two-step crystallization processes. From the Fig. 1(a), the amorphous $\text{Ge}_2\text{Sb}_2\text{Te}_5$ thin film was crystallized into the face-centered-cubic (fcc) structure at about 160 °C. After annealing at 260 °C, the fcc structure was transformed to hexagonal (hcp) structure. However, the structure of N-GST thin films differed from that of GST. In the case of the N (=2, 4 sccm)-doped GST thin films, amorphous phase was maintained up to 200 °C and N (=6 sccm)-doped GST thin film was 260 °C. In addition, when contents of nitrogen increased, crystallized peaks appear to be broader in width and lower in intensity as shown in Fig. 1. Considering that a peak shape of XRD relates to crystalline grain size, the nitrogen doped into GST can be evaluated to serve as a center to suppress crystalline grain growth, resulting in an increase in the crystallization temperature, T_C , as shown in Fig. 1(b)-(d). [9-10] In particular, the realization of high T_C leads to an improvement of thermal stability in amorphous state, one of important factors in PRAM devices.

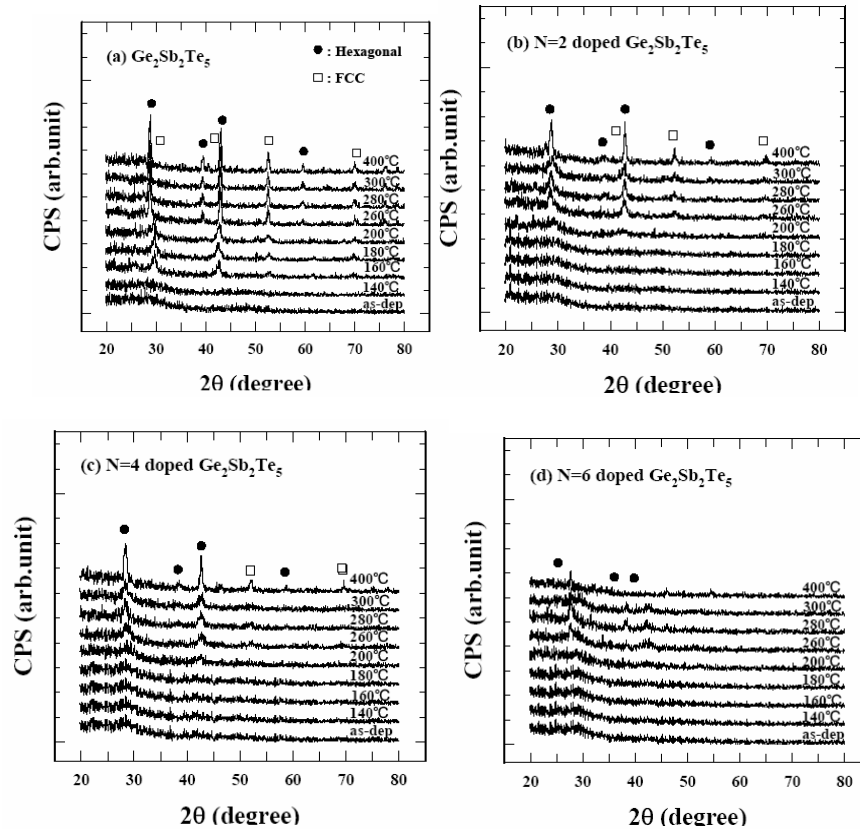


Fig. 1 XRD patterns of 200-nm-thick (a) $\text{Ge}_2\text{Sb}_2\text{Te}_5$, (b) $\text{N} = 2$ sccm doped, (c) $\text{N} = 4$ sccm doped and (d) $\text{N} = 6$ sccm doped $\text{Ge}_2\text{Sb}_2\text{Te}_5$ thin films as a function of the annealing temperature. The peak marked by the blank (\square) and filled (\bullet) correspond to fcc and hcp phases, respectively.

The GST and N-GST thin films were crystallized by annealing at 260 °C for 10 min and their surface morphology observed by AFM was displayed in Fig. 2, where the scale bar on the y-axis of (d) is very large in comparison with those of (a)~(c). As shown in Figs. 2(a) ~ 2(c), the surface morphology appears to be relatively more smooth with increasing N-contents. That is, the crystalline

grain size can be evaluated to decrease with increasing N-contents as discussed in Fig. 1. However, as shown in Fig. 2(d), the hillocks were observed on the surface of N (=6 sccm)-doped GST thin film. It could be considered that these hillocks result from the press of nitrides condensed near grain boundaries.[11]

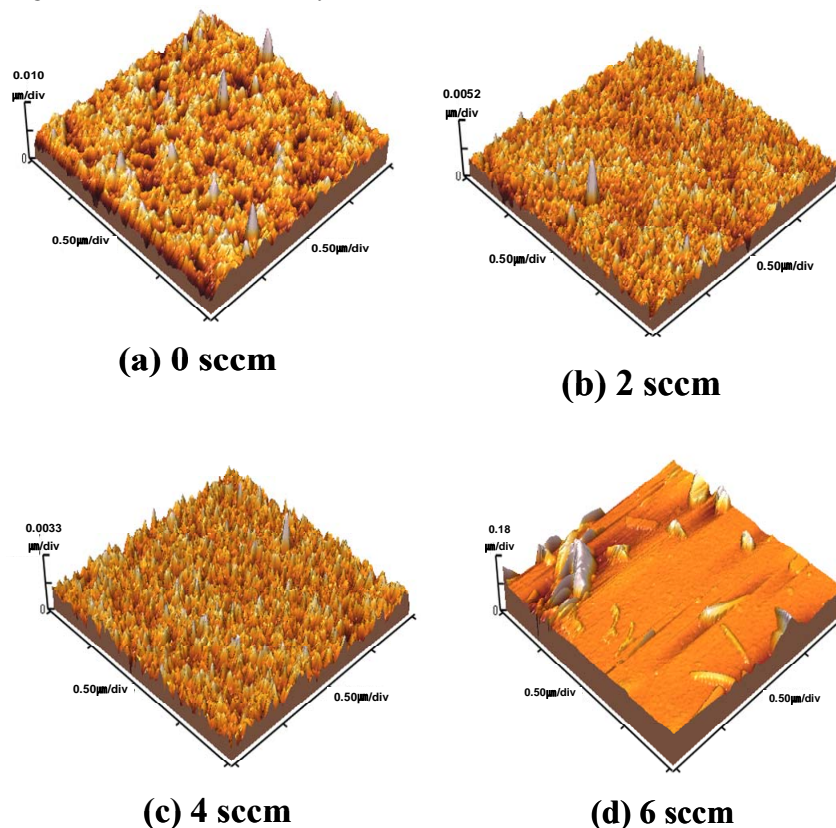


Fig. 2 AFM images of the N-doped $Ge_2Sb_2Te_5$ thin films annealed at 260 °C for 10 min. The various N contents were (a) 0 sccm, (b) 2 sccm, (c) 4 sccm and (d) 6 sccm. The scale bars on the y-axis is very different; (a) 0.1 $\mu\text{m}/\text{div}$, (b) 0.0052 $\mu\text{m}/\text{div}$, (c) 0.0033 $\mu\text{m}/\text{div}$ and (d) 0.18 $\mu\text{m}/\text{div}$.

The grain size reduction, seen from Figs. 2(b) and 2(c), resulted from the formation of the nitrides like Ge-N, Sb-N and Te-N. [12] This grain size reduction brings about increase of sheet resistance (Fig. 4). Considering that a large change in grain size may deteriorate reliability in the reversible phase-change data storage, N-GST(=2, 4 sccm) film can be evaluated as a candidate material to improve the reliability of PRAM. [4] Quantitative values of surface roughness in the crystallized films (Fig. 2) are shown in Fig. 3 as a function of N_2 -gas flow rate. The roughness slightly decreased with increasing the N_2 -gas flow rate from 0 to 4 sccm but abruptly increased in 6 sccm. That is, a proper N doping (2 and 4 sccm in this work) is effective for smoothing the surface of the crystalline GST film.

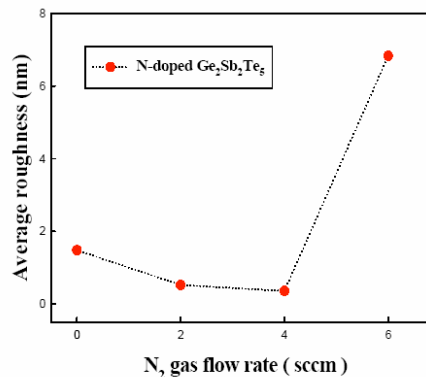


Fig. 3 Average RMS roughness of the N-doped $Ge_2Sb_2Te_5$ thin films annealed at 260 °C for 10 min.

The temperature-dependent sheet resistance (R_S) of phase change material is an important factor. The 4-point probe method was utilized to study the R_S -dependence of the GST and N-GST films according to annealing temperature and displayed in Fig. 4. The 200-nm-thick GST and N-GST films were annealed in a 200 sccm N₂ atmosphere for 10 min at the temperature ranges of 100 ~ 400 °C, heating rate (dT/dt) ~ 5.0 K/min.

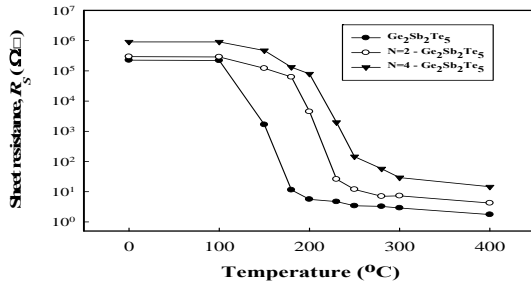


Fig. 4 Changes in sheet resistance (R_S) on annealing temperature for the 200-nm-thick Ge₂Sb₂Te₅ and N-doped Ge₂Sb₂Te₅ films. Films were annealed in a N₂ ambient for 10 min at 100 ~ 400 °C (heating rate ~ 5.0 K/min).

As shown in Fig. 4, the as-deposited GST film (●) of amorphous state showed a high R_S of ~10⁵ Ω/□. After annealing at 150 °C, the R_S -value was drastically reduced to ~ 10¹ Ω/□, which indicates amorphous-to-crystalline (fcc) phase transition. The R_S of 10¹ Ω/□ corresponds to the resistivity of 2 × 10⁻⁴ Ωcm. The incorporation of nitrogen into the GST films increases the R_S for the overall temperature ranges. In particular, R_S of the N (=4 sccm) GST films (▼) on the crystalline-phase region (200~400 °C) was higher by one order in comparison with that of GST film. This is related to the grain size reduction by N doping as explained in Fig. 2. The R_S -dependence on the grain size can be explained as grain boundary scattering mechanism.[13] In addition, although R_S -values of N-GST were higher than those of the GST, The amorphous/crystalline resistance ratio was constant to be ~10⁵. Conclusively, the N-doping causes an increase of R_S for both amorphous and crystalline phases at all annealed temperatures, which is useful to reduce programming (SET and RESET) current. As shown in Figs. 2 and 4, high T_C -values obtained by the N doping results in the improvement of thermal stability on the amorphous phase.

Amorphous chalcogenides with a strong electron-lattice interaction obey the absorption properties expressed as $\alpha hv = B(hv - E_{OP})^n$ for the extended energy region ($hv > E_{OP}$) in which $B^{1/2}$ is the slope in the extended region ($hv > E_{OP}$) and lies in the range ~ 10³ cm^{-1/2} eV^{-1/2} [14-17]. The exponent n is an appropriately selected index, which depends on the nature of electronic transition and can be assumed to have a value of either 1/2 or 2 for the direct transition and the indirect transition, respectively [18].

Many papers have shown n = 2 acceptable for amorphous chalcogenide semiconductors, including Ge, GeTe, GeSbTe, etc [19-22]. Therefore, E_{OP} is obtained from the intercept on the energy axis of the plot $(\alpha hv)^{1/2}$ vs. hv as shown in Fig. 5(a). That is, E_{OP} of GST was evaluated to be ~ 0.67 eV. The quantities of E_{OP} in the GST and N-GST films were indicated in Fig. 5(b) as a function of the amount of incorporated nitrogen. The incorporation of nitrogen, which mainly formed Ge-N bonds in the GST film [7], increased E_{OP} in proportion to the amount of N-contents

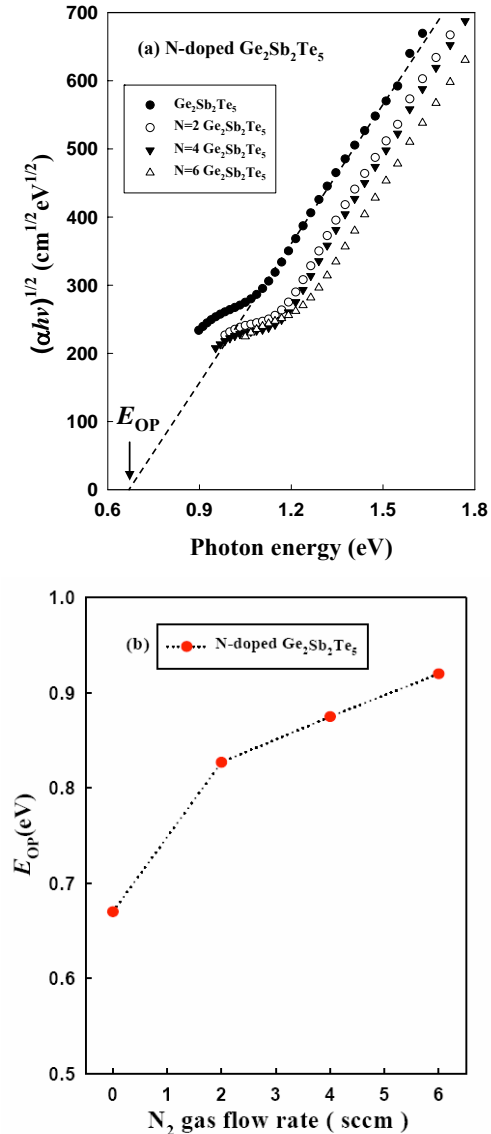


Fig. 5 (a) Plots $(\alpha hv)^{1/2}$ vs. hv for N-doped Ge₂Sb₂Te₅ thin films : N=0 sccm(●), N=2 sccm(○), N=4 sccm(▼) and N=6 sccm(△). The optical energy gap (E_{OP}) was obtained from the intercept on the energy axis of the plot. (b) Change in E_{OP} of N-GST films as functions of the amount of incorporated nitrogen.

To investigate the crystallization kinetics on the nanosecond scales, a nano-pulse scanner was employed. The illumination energy by the nano-pulse scanner is systematically controlled as a function of laser power (P) and pulse duration (t) at each pulse. By this method, the phase transition can be deduced from the changes in

reflectivity. Three-dimensional (3D) mesh plots for the nano-pulse reflection response in the GST and N-GST thin films with increasing P and t are shown in Fig. 6, where ΔR is the reflection difference ($R_2 - R_1$).

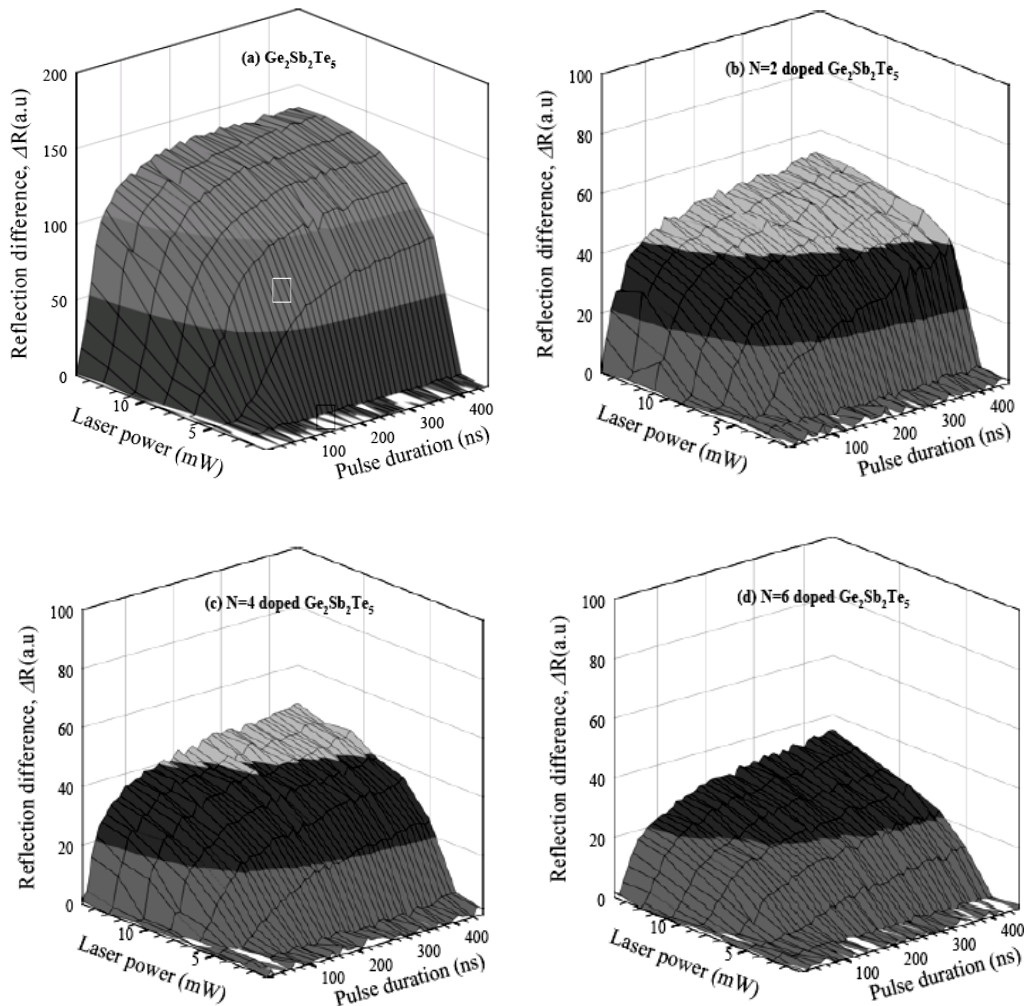


Fig. 6 3D mesh plots for nano-pulse reflection response in the N-SGT ($N=0, 2, 4, 6$ sccm) thin films. The symbol I and II in (a) represent the amorphous and crystalline regions, respectively. The reflection difference ΔR is $R_1 - R_2$, where R_1 and R_2 are the intensities before and after illumination, respectively. In this work, ΔR was measured in a laser power ranges of 1-17 mW and a pulse duration ranges of 10-460 ns.

The insufficient P and t illumination does not generate any change in optical properties (region I). The crystallization (region II) occurs for a proper combination of P and t . That is, the ΔR value in region I becomes nearly 0 since the power was too low and/or the pulse was

too short to achieve crystallization. ΔR in region-II is positive and the film corresponds to a crystalline. As shown Fig. 6, the slopes of ΔR vs P and t for N-GST films (b, c, d) distinctly decreased compared to that of GST film (a) because the nitride disturbs the crystallization.

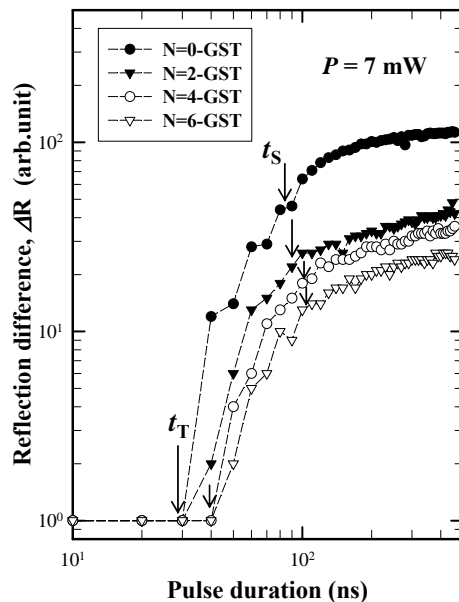


Fig. 7 Log-scaled plot of ΔR vs pulse duration (t) for a relatively low power (7 mW). The arrows represent the sensitivity t_s and the threshold pulse duration t_T .

Figure 7 shows the log-scaled plot of ΔR vs t for a relatively low power (7 mW). Here the arrows represent the sensitivity t_s defined as a pulse duration corresponding to 50% of the maximum ΔR , and t_T indicates the threshold pulse duration. The nitrogen doping into the GST increased the values of t_T and t_s as well as lowered the maximum ΔR . For the GST film, t_T and t_s were evaluated to be approximately 30 ns and 83 ns, respectively. The t_T and t_s values of the N (=4 sccm)-GST film were 40 ns and 98 ns. Therefore, although nitrogen doping into the GST improves the thermal stability on amorphous state and the sheet resistance of both amorphous and crystalline phases, the speed of amorphous-to-crystalline transition is deteriorated.

4. Conclusions

We have investigated influence of nitrogen on the amorphous-crystalline phase transition in the GST thin films. The nitrogen effects can be summarized as follows. According to XRD results, crystallized peaks appear to be broader in width and lower in intensity by doping nitrogen, which shows the crystallization temperature increased. Compared with the GST, N-GST showed higher sheet resistance of both amorphous and crystalline phase because of the grain size reduction. It is useful to reduce programming current. However, the speed of amorphous-to-crystalline transition is relatively very slow by adding nitrogen into the GST. It is considered that the nitrides condense near grain boundaries and have a suppressing effect in the crystallization growth.

In conclusion, although nitrogen doping into GST is a very effective for increasing thermal stability on amorphous state and the sheet resistance of both amorphous and crystalline phases, the speed of amorphous-to-crystalline transition is deteriorated. We propose that the nitrogen into GST plays a role to suppress amorphous-to-crystalline phase transition.

Acknowledgments

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